

Title (en)

EDGE-EMITTING SEMICONDUCTOR TUNABLE LASER

Title (de)

VERSTIMMBARER RANDEMITTIERENDER HALBLEITERLASER

Title (fr)

LASER ACCORDABLE EN SEMI-CONDUCTEUR A EMISSION PAR LA TRANCHE

Publication

EP 1307955 A2 20030507 (FR)

Application

EP 01963053 A 20010802

Priority

- FR 0102530 W 20010802
- FR 0010366 A 20000804

Abstract (en)

[origin: WO0213335A2] The invention concerns an edge-emitting semiconductor tunable laser (10) comprising a resonant cavity delimited by two reflectors (15, 20) one of which is fixed (15) and the other mobile (20), said cavity consisting of a first active gain section (1) with length L1 and a second tunable section of length L2. The invention is characterised in that the total length of the cavity L = to L1+L2 is not more than 20 mu m.

IPC 1-7

H01S 5/14

IPC 8 full level

H01S 5/062 (2006.01); **H01S 5/14** (2006.01); **H01S 5/02** (2006.01); **H01S 5/10** (2006.01); **H01S 5/125** (2006.01)

CPC (source: EP US)

H01S 5/14 (2013.01 - EP US); **H01S 3/105** (2013.01 - EP US); **H01S 5/0203** (2013.01 - EP US); **H01S 5/02325** (2021.01 - EP US); **H01S 5/1039** (2013.01 - EP US); **H01S 5/125** (2013.01 - EP US)

Citation (search report)

See references of WO 0213335A2

Designated contracting state (EPC)

AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE TR

DOCDB simple family (publication)

WO 0213335 A2 20020214; **WO 0213335 A3 20020502**; EP 1307955 A2 20030507; FR 2812769 A1 20020208; FR 2812769 B1 20030829; JP 2004506334 A 20040226; US 2002151126 A1 20021017; US 6865195 B2 20050308

DOCDB simple family (application)

FR 0102530 W 20010802; EP 01963053 A 20010802; FR 0010366 A 20000804; JP 2002518583 A 20010802; US 8956902 A 20020402